

P-Channel Enhancement Mode Power MOSFET

Description

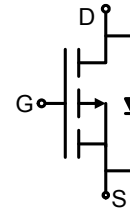
The PE30P80K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

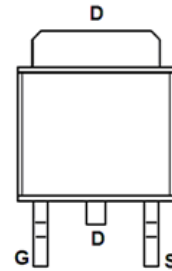
- $V_{DS} = -30V, I_D = -80A$
 $R_{DS(ON)} < 5.5m\Omega @ V_{GS} = -10V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

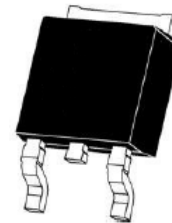
- Battery and loading switching



Schematic diagram



Marking and pin assignment



TO-252 -2Ltop view

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-80	A
Pulsed Drain Current	I_{DM}	-100	A
Maximum Power Dissipation	P_D	70	W
Derating factor		0.5	W/ $^\circ C$
Single pulse avalanche energy ^(Note 5)	E_{AS}	200	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	2.0	$^\circ C/W$
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Electrical Characteristics (TC=25°C unless otherwise noted)

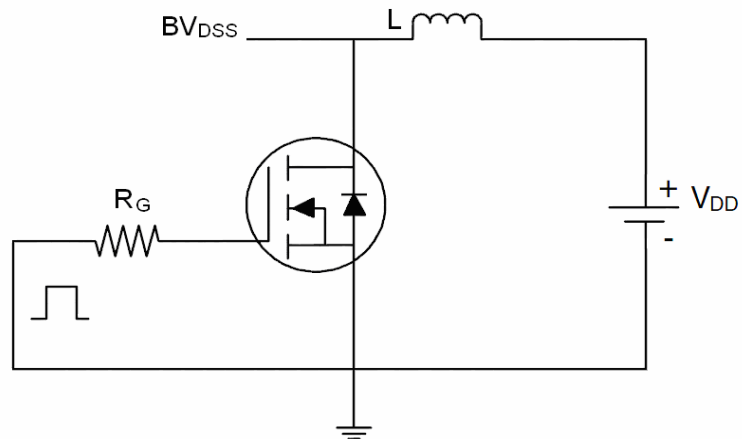
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.5	-2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-10A	-	4.4	5.5	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-15A	-	20	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V, F=1.0MHz	-	3590	-	PF
Output Capacitance	C _{oss}		-	695	-	PF
Reverse Transfer Capacitance	C _{rss}		-	665	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V, I _D =-10A V _{GS} =-10V, R _{GEN} =6Ω	-	13	-	nS
Turn-on Rise Time	t _r		-	12	-	nS
Turn-Off Delay Time	t _{d(off)}		-	50	-	nS
Turn-Off Fall Time	t _f		-	14	-	nS
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-10A, V _{GS} =-10V	-	84	-	nC
Gate-Source Charge	Q _{gs}		-	11.7	-	nC
Gate-Drain Charge	Q _{gd}		-	25	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =-10A	-	-0.85	-1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	-50	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = -10A di/dt = 100A/μs(Note3)	-	-	45	nS
Reverse Recovery Charge	Q _{rr}		-	-	43	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

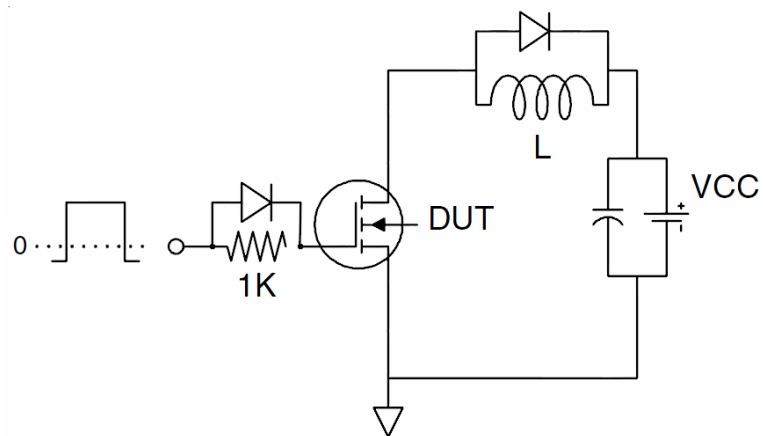
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^\circ C, V_{DD}=-15V, V_G=-10V, L=0.5mH, R_g=25\Omega$

Test Circuit

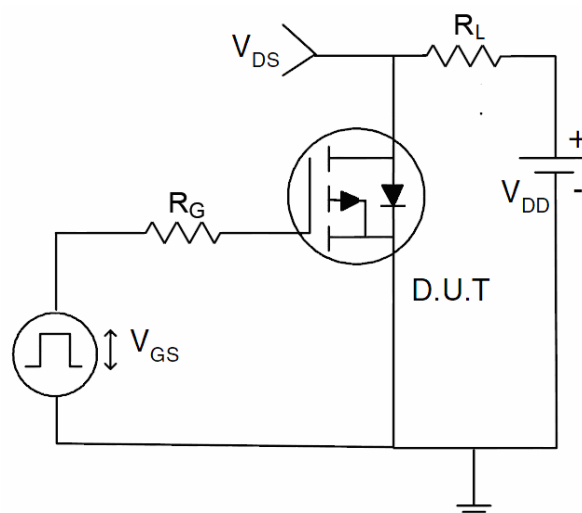
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

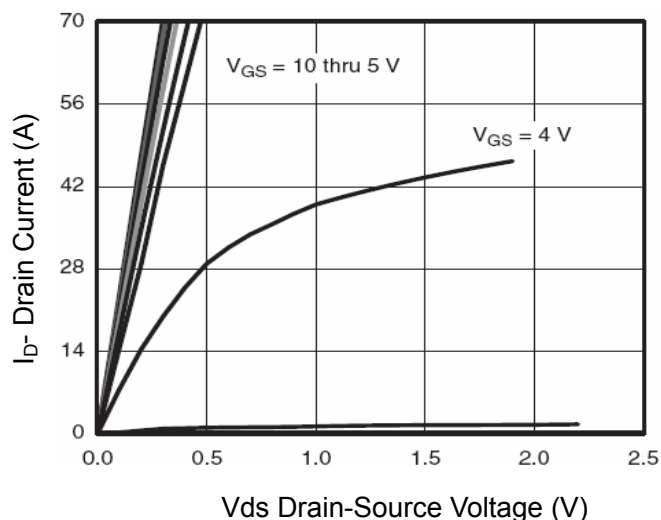


Figure 1 Output Characteristics

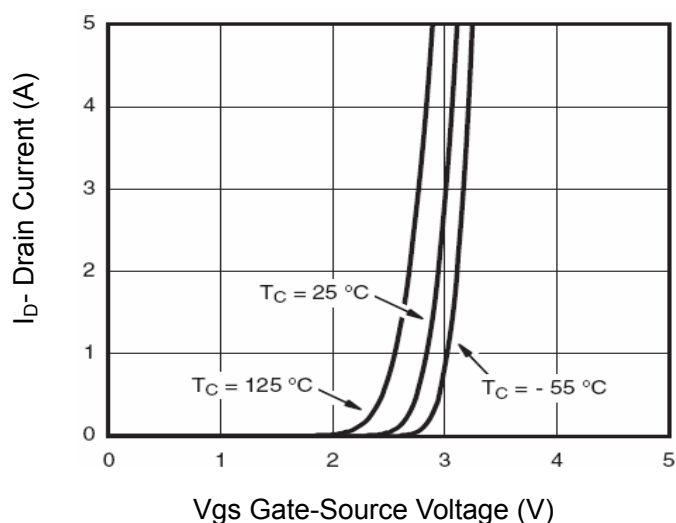


Figure 2 Transfer Characteristics

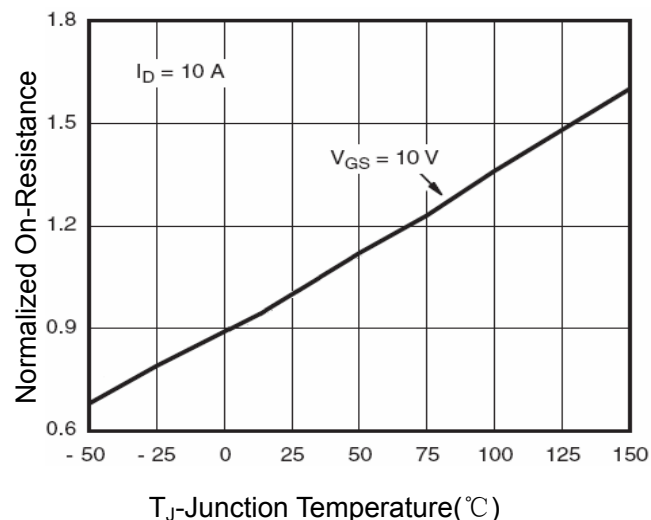


Figure 4 $R_{DS(on)}$ -Junction Temperature

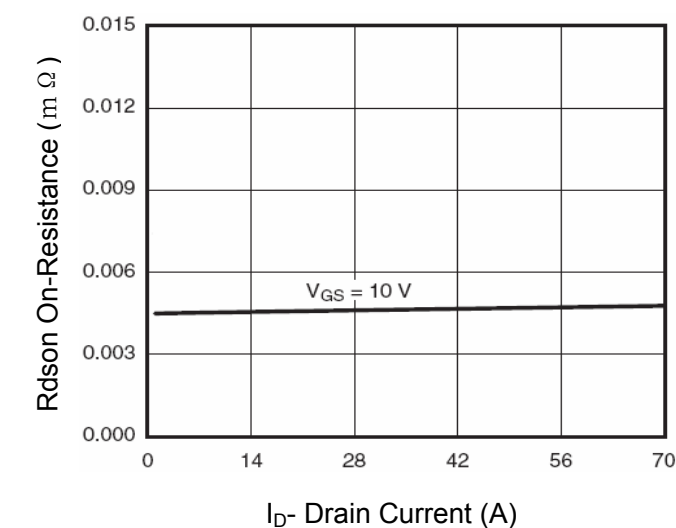


Figure 3 $R_{DS(on)}$ - Drain Current

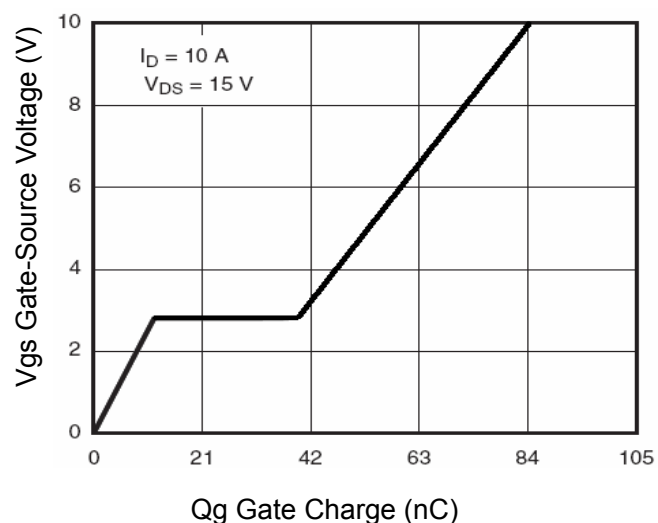


Figure 5 Gate Charge

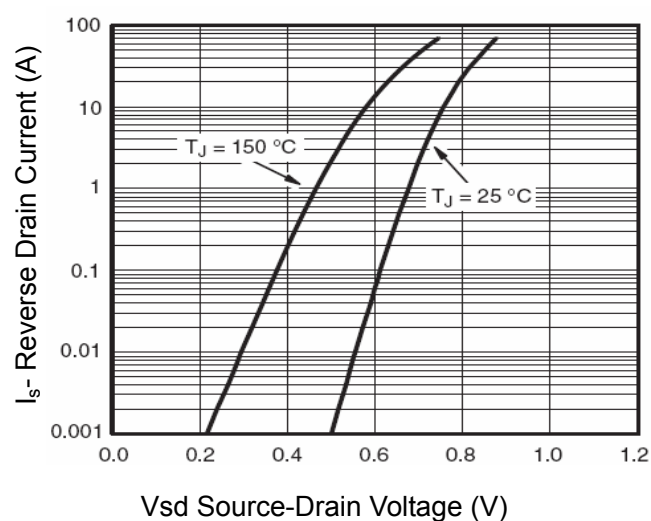
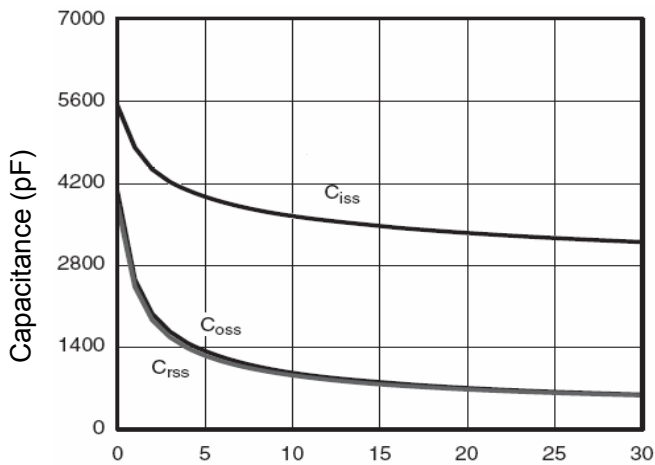
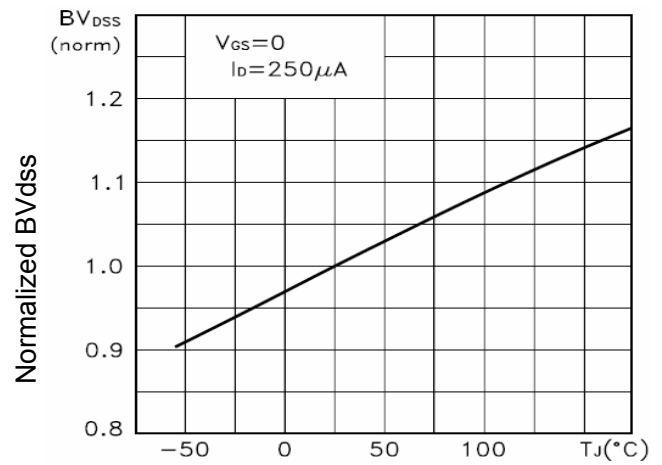


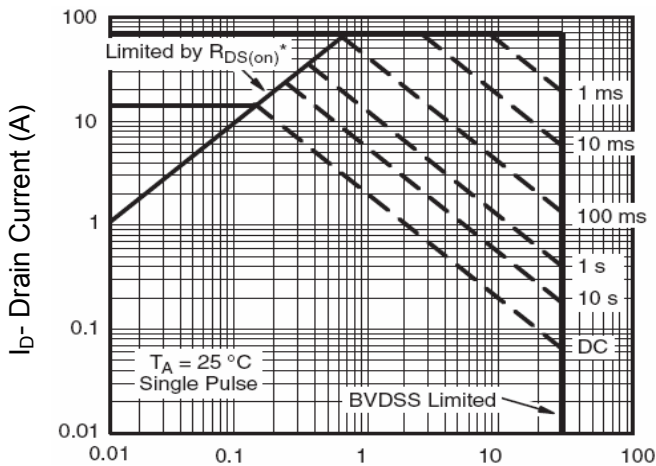
Figure 6 Source- Drain Diode Forward



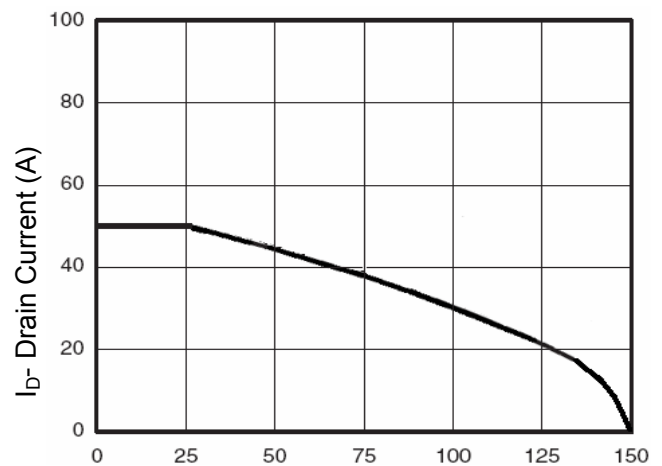
Vds Drain-Source Voltage (V)
Figure 7 Capacitance vs Vds



TJ-Junction Temperature(°C)
Figure 9 BV_{DSS} vs Junction Temperature



Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area



TJ-Junction Temperature(°C)
Figure 10 ID Current Derating vs Junction Temperature

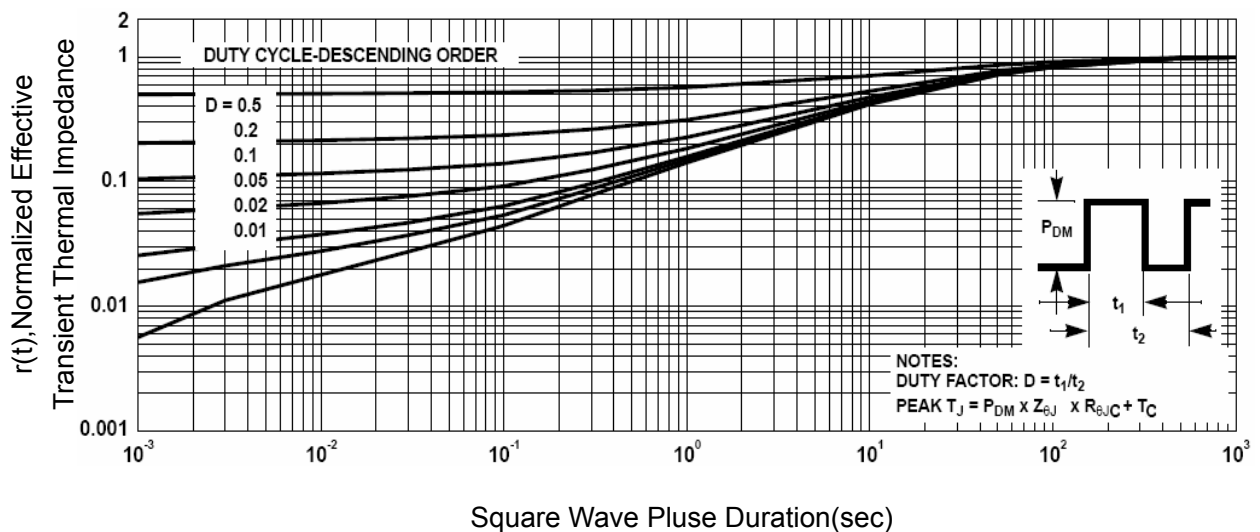
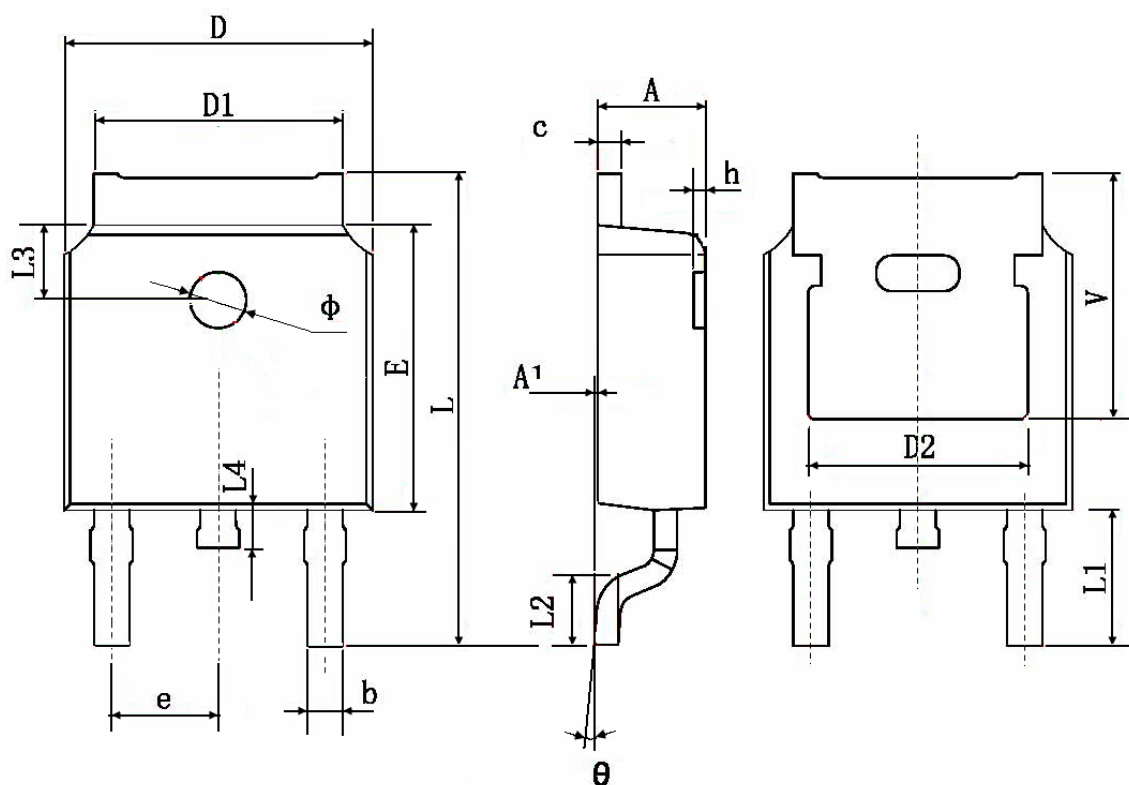


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	